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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	S08
Core Size	8-Bit
Speed	20MHz
Connectivity	-
Peripherals	LVD, POR, PWM, WDT
Number of I/O	4
Program Memory Size	4KB (4K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256 x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 4x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	8-VDFN Exposed Pad
Supplier Device Package	8-DFN-EP (4x4)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mc9s08qa4cfqe

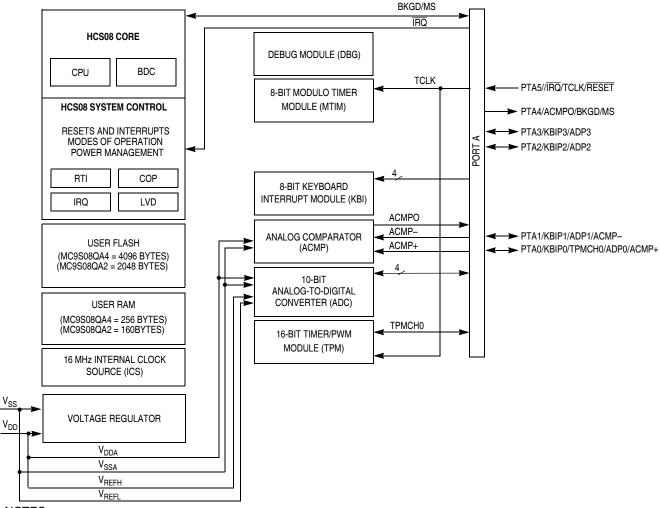
Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



1 MCU Block Diagram

The block diagram, Figure 1, shows the structure of the MC9S08QA4 MCU.



NOTES:

- 1 Port pins are software configurable with pullup device if input port.
- ² Port pins are software configurable for output drive strength.
- ³ Port pins are software configurable for output slew rate control.
- ⁴ IRQ contains a software configurable (IRQPDD) pullup device if PTA5 enabled as IRQ pin function (IRQPE = 1).
- ⁵ RESET contains integrated pullup device if PTA5 enabled as reset pin function (RSTPE = 1).
- ⁶ PTA4 contains integrated pullup device if BKGD enabled (BKGDPE = 1).
- When pin functions as KBI (KBIPEn = 1) and associated pin is configured to enable the pullup device, KBEDGn can be used to reconfigure the pullup as a pulldown device.

Figure 1. MC9S08QA4 Series Block Diagram

2 Pin Assignments

This section shows the pin assignments in the packages available for the MC9S08QA4 series.



A device is defined as a failure if after exposure to ESD pulses the device no longer meets the device specification. Complete DC parametric and functional testing is performed per the applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

Table 4. ESD and Latch-up Test Conditions

Model	Description	Symbol	Value	Unit
	Series resistance	R1	1500	Ω
Human Body	Storage capacitance	С	100	pF
	Number of pulses per pin		3	
	Series resistance	R1	0	Ω
Machine	Storage capacitance	С	200	pF
	Number of pulses per pin		3	
Latch-up	Minimum input voltage limit		-2.5	V
Lateri-up	Maximum input voltage limit		7.5	٧

Table 5. ESD and Latch-Up Protection Characteristics

No.	Rating ¹	Symbol	Min	Max	Unit
1	Human body model (HBM)	V_{HBM}	±2000	_	V
2	Machine model (MM)	V_{MM}	±200	_	V
3	Charge device model (CDM)	V _{CDM}	±500	_	V
4	Latch-up current at T _A = 85°C	I _{LAT}	±100	_	mA

Parameter is achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted.

3.5 DC Characteristics

This section includes information about power supply requirements and I/O pin characteristics.

Table 6. DC Characteristics (Temperature Range = −40 to 85°C Ambient)

Parameter	Symbol	Min	Typical	Max	Unit
Supply voltage (run, wait, and stop modes)					
(V _{DD} falling)	V_{DD}	1.8	_	3.6	V
(V _{DD} rising)		V _{LVDL} (rising)	_	3.6	
Minimum RAM retention supply voltage applied to V _{DD}	V _{RAM}	V _{por} ^{1,2}	_	_	V
Low-voltage detection threshold					
(V _{DD} falling)	V_{LVD}	1.80	1.82	1.91	v
(V _{DD} rising)		1.88	1.90	1.99	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
Low-voltage warning threshold (V _{DD} falling)	V _{LVW}	2.08	2.1	2.2	V



Table 6. DC Characteristics (Temperature Range = -40 to 85°C Ambient) (continued)

Parameter	Symbol	Min	Typical	Max	Unit
(V _{DD} rising)		2.16	2.19	2.27	
Power on reset (POR) re-arm voltage	V _{por}	_	1.4	_	٧
Bandgap voltage reference	V_{BG}	1.18	1.20	1.21	V
Input high voltage (V _{DD} > 2.3 V) (all digital inputs)	V	$0.70 \times V_{DD}$	_	_	٧
Input high voltage (1.8 V \leq V _{DD} \leq 2.3 V) (all digital inputs)	V_{IH}	$0.85 \times V_{DD}$	_	_	V
Input low voltage (V _{DD} > 2.3 V) (all digital inputs)	V	_	_	$0.35 \times V_{DD}$	٧
Input low voltage (1.8 V \leq V _{DD} \leq 2.3 V) (all digital inputs)	V_{IL}	_	_	$0.30 \times V_{DD}$	V
Input hysteresis (all digital inputs)	V _{hys}	$0.06 \times V_{DD}$	_	_	٧
Input leakage current (per pin) $V_{In} = V_{DD}$ or V_{SS} , all input-only pins	I _{In}	_	0.025	1.0	μΑ
High impedance (off-state) leakage current (per pin) $V_{In} = V_{DD}$ or V_{SS} , all input/output	II _{OZ} I	_	0.025	1.0	μА
Internal pullup resistors ^{3,4}	R _{PU}	17.5	_	52.5	kΩ
Internal pulldown resistor (KBI)	R _{PD}	17.5	_	52.5	kΩ
Output high voltage — low drive (PTxDSn = 0) $I_{OH} = -2 \text{ mA } (V_{DD} \ge 1.8 \text{ V})$		V _{DD} – 0.5	_	_	
Output high voltage — high drive (PTxDSn = 1) $I_{OH} = -10 \text{ mA } (V_{DD} \ge 2.7 \text{ V})$ $I_{OH} = -6 \text{ mA } (V_{DD} \ge 2.3 \text{ V})$ $I_{OH} = -3 \text{ mA } (V_{DD} \ge 1.8 \text{ V})$	V _{OH}	V _{DD} – 0.5	_ _ _	_ _ _	V
Maximum total I _{OH} for all port pins	II _{OHT} I	_	_	60	mA
Output low voltage — low drive (PTxDSn = 0) I_{OL} = 2.0 mA ($V_{DD} \ge 1.8 \text{ V}$)		_	_	0.5	V
Output low voltage — high drive (PTxDSn = 1) $I_{OL} = 10.0 \text{ mA } (V_{DD} \ge 2.7 \text{ V})$ $I_{OL} = 6 \text{ mA } (V_{DD} \ge 2.3 \text{ V})$ $I_{OL} = 3 \text{ mA } (V_{DD} \ge 1.8 \text{ V})$	V _{OL}	_ _ _	_ _ _	0.5 0.5 0.5	V
Maximum total I _{OL} for all port pins	I _{OLT}	_	_	60	mA
DC injection current $^{2, 5, 6, 7}$ $V_{ln} < V_{SS}, V_{ln} > V_{DD}$ Single pin limit Total MCU limit, includes sum of all stressed pins	I _{IC}	-0.2 -5	_ _	0.2 5	mA mA
Input capacitance (all non-supply pins)	C _{In}	_	_	7	pF
· ·		•			

¹ RAM will retain data down to POR voltage. RAM data not guaranteed to be valid following a POR.

² This parameter is characterized and not tested on each device.

 $^{^3}$ Measurement condition for pull resistors: $\rm V_{In} = \rm V_{SS}$ for pullup and $\rm V_{In} = \rm V_{DD}$ for pulldown.

⁴ PTA5/IRQ/TCLK/RESET pullup resistor may not pull up to the specified minimum V_{IH}. However, all ports are functionally tested to guarantee that a logic 1 will be read on any port input when the pullup is enabled and no DC load is present on the pin.

 $^{^{\}rm 5}$ All functional non-supply pins are internally clamped to $\rm V_{SS}$ and $\rm V_{DD}$



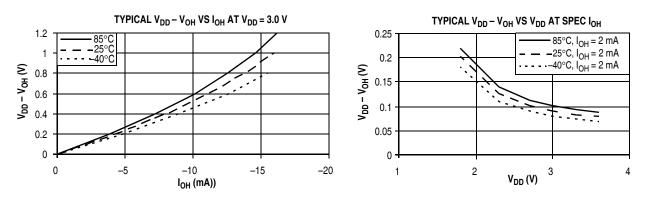


Figure 6. Typical High-Side (Source) Characteristics — Low Drive (PTxDSn = 0)

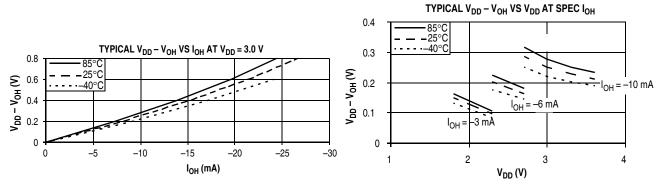


Figure 7. Typical High-Side (Source) Characteristics — High Drive (PTxDSn = 1)

3.6 Supply Current Characteristics

This section includes information about power supply current in various operating modes.

Table 7. Supply Current Characteristics

Parameter	Symbol	V _{DD} (V) ¹	Typical ²	Max	T (°C)
Run supply current ³ measured in FBE mode at	RI _{DD}	3	3.5 mA	5 mA	85
$f_{Bus} = 8 \text{ MHz}$	TUDD	2	2.6 mA	_	85
Run supply current ³ measured in FBE mode at	RI _{DD}	3	490 μΑ	1 mA	85
$f_{Bus} = 1 \text{ MHz}$	тирр	2	370 μΑ	_	85
Wait mode supply current4 measured in FBE at 8 MHz	WI _{DD}	3	1 mA	1.5 mA	85
Stop1 mode supply current	S1I _{DD}	3	475 nA	1.2 μΑ	85
		2	470 nA	_	85
Stop2 mode supply current	Sal	3	600 nA	2 μΑ	85
	S2I _{DD}	2	550 nA	_	85
Stop3 mode supply current	631	3	750 nA	6 μΑ	85
	S3I _{DD}	2	680 nA	_	85
RTI adder to stop1, stop2, or stop3 ⁴		3	300 nA	_	85
		2	300 nA	_	85
LVD adder to stop3 (LVDE = LVDSE = 1)4		3	70 μΑ	_	85
		2	60 μΑ	_	85

MC9S08QA4 Series MCU Data Sheet, Rev. 3



- ¹ 3 V values are 100% tested; 2 V values are characterized but not tested.
- 2 Typicals are measured at 25 $^{\circ}\text{C}.$
- ³ Does not include any DC loads on port pins.

3.7 Internal Clock Source (ICS) Characteristics

Table 8. ICS Specifications (Temperature Range = −40 to 85°C Ambient)

Characteristic	Symbol	Min	Typical ¹	Max	Unit
Internal reference start-up time	t _{IRST}	_	60	100	μS
Average internal reference frequency — untrimmed	f _{int_ut}	25	32.7	41.66	kHz
Average internal reference frequency — trimmed	f _{int_t}	31.25	_	39.06	kHz
DCO output frequency range — untrimmed	f _{dco_ut}	12.8	16.8	21.33	MHz
DCO output frequency range — trimmed	f _{dco_t}	16	_	20	MHz
Resolution of trimmed DCO output frequency at fixed voltage and temperature ²	Δf _{dco_res_t}	_	±0.1	±0.2	%f _{dco}
Total deviation of DCO output from trimmed frequency ² At 8 MHz over full voltage and temperature range At 8 MHz and 3.6 V from 0 to 70 °C	Δf_{dco_t}	_	-1.0 to 0.5 ±0.5	±2 ±1	%f _{dco}
FLL acquisition time ^{2,3}	t _{Acquire}	_	_	1.5	ms
Long term jitter of DCO output clock (averaged over 2 ms interval)	C _{Jitter}	_	0.02	0.2	%f _{dco}

¹ Data in Typical column was characterized at 3.0 V, 25 °C, or is typical recommended value.

⁴ Most customers are expected to find that auto-wakeup from a stop mode can be used instead of the higher current wait mode.

² This parameter is characterized and not tested on each device.

³ This specification applies to any time the FLL reference source or reference divider is changed, trim value changed.



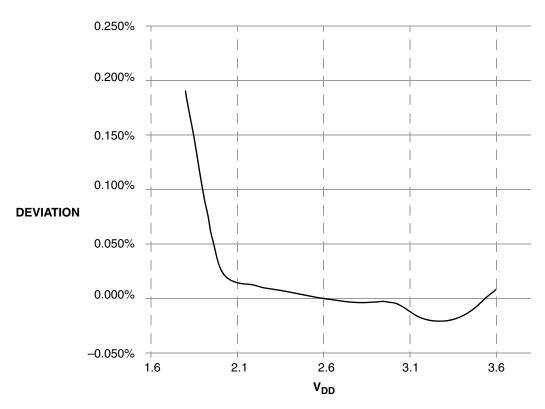


Figure 8. Deviation of DCO Output from Trimmed Frequency (8 MHz, 25 $^{\circ}$ C)

3.8 AC Characteristics

This section describes timing characteristics for each peripheral system.



3.8.1 Control Timing

Table 9. Control Timing

Parameter	Symbol	Min	Typical ¹	Max	Unit
Bus frequency (t _{cyc} = 1/f _{Bus})	f _{Bus}	0	_	10	MHz
Real-time interrupt internal oscillator period (see Table 9)	t _{RTI}	700	1000	1300	μS
External reset pulse width ²	t _{extrst}	100	_	_	ns
IRQ pulse width Asynchronous path ² Synchronous path ³	t _{ILIH}	100 1.5 t _{cyc}	_	_	ns
KBIPx pulse width Asynchronous path ² Synchronous path ³	t _{ILIH} , t _{IHIL}	100 1.5 t _{cyc}	_	_	ns
Port rise and fall time (load = 50 pF) ⁴ Slew rate control disabled (PTxSE = 0) Slew rate control enabled (PTxSE = 1)	t _{Rise} , t _{Fall}		3 30		ns
BKGD/MS setup time after issuing background debug force reset to enter user or BDM modes	t _{MSSU}	500	_	_	ns
BKGD/MS hold time after issuing background debug force reset to enter user or BDM modes ⁵	t _{MSH}	100	_	_	μS

¹ Data in Typical column was characterized at 3.0 V, 25°C.

⁵ To enter BDM mode following a POR, BKGD/MS should be held low during the power-up and for a hold time of t_{MSH} after V_{DD} rises above V_{LVD}.

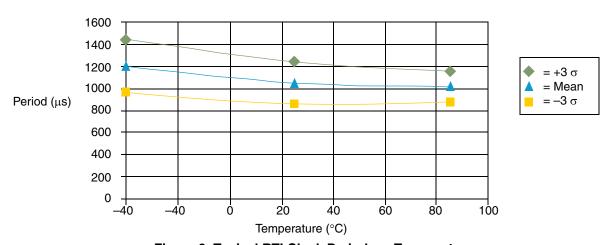


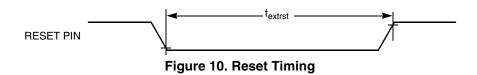
Figure 9. Typical RTI Clock Period vs. Temperature

 $^{^{2}\,}$ This is the shortest pulse that is guaranteed to be recognized.

³ This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In stop mode, the synchronizer is bypassed so shorter pulses can be recognized in that case.

 $^{^4}$ Timing is shown with respect to 20% $\rm V_{DD}$ and 80% $\rm V_{DD}$ levels. Temperature range $-40^{\circ} \rm C$ to 85°C.





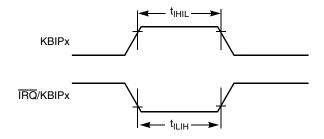


Figure 11. IRQ/KBIPx Timing

3.8.2 TPM/MTIM Module Timing

Synchronizer circuits determine the shortest input pulses that can be recognized or the fastest clock that can be used as the optional external source to the timer counter. These synchronizers operate from the current bus rate clock.

Table 10. TPM/MTIM Input Timing

Function	Symbol	Min	Max	Unit
External clock frequency	f _{TCLK}	0	f _{Bus} /4	Hz
External clock period	t _{TCLK}	4	_	t _{cyc}
External clock high time	t _{clkh}	1.5	_	t _{cyc}
External clock low time	t _{clkl}	1.5	_	t _{cyc}
Input capture pulse width	t _{ICPW}	1.5	_	t _{cyc}

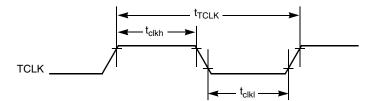


Figure 12. Timer External Clock



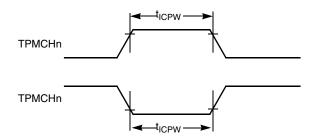


Figure 13. Timer Input Capture Pulse

3.9 Analog Comparator (ACMP) Electricals

Table 11. Analog Comparator Electrical Specifications

Characteristic	Symbol	Min	Typical	Max	Unit
Supply voltage	V_{DD}	1.80	_	3.60	٧
Supply current (active)	I _{DDAC}	_	20	_	μΑ
Analog input voltage	V _{AIN}	V _{SS} – 0.3	_	V_{DD}	V
Analog input offset voltage	V _{AIO}	_	20	40	mV
Analog comparator hysteresis	V _H	3.0	9.0	15.0	mV
Analog input leakage current	I _{ALKG}	_	_	1.0	μΑ
Analog comparator initialization delay	t _{AINIT}	_	_	1.0	μS

3.10 ADC Characteristics

Table 12. 3 V 10-Bit ADC Operating Conditions

Characteristic	Conditions	Symbol	Min	Typical ¹	Max	Unit	Comment
Supply voltage	Absolute	V_{DD}	1.8	_	3.6	V	
Input voltage		V _{ADIN}	V _{SS}	_	V_{DD}	V	
Input capacitance		C _{ADIN}	_	4.5	5.5	pF	
Input resistance		R _{ADIN}	_	5	7	kΩ	
Analog source resistance	10 bit mode f _{ADCK} > 4 MHz f _{ADCK} < 4 MHz	R _{AS}	_ _	_ _	5 10	kΩ	External to MCU
	8 bit mode (all valid f _{ADCK})		_	_	10		
ADC conversion	High Speed (ADLPC=0)	f	0.4	_	8.0	MHz	
clock frequency	Low Power (ADLPC=1)	f _{ADCK}	0.4	_	4.0	IVIMZ	

Typical values assume V_{DD} = 3.0 V, Temp = 25°C, f_{ADCK} =1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.



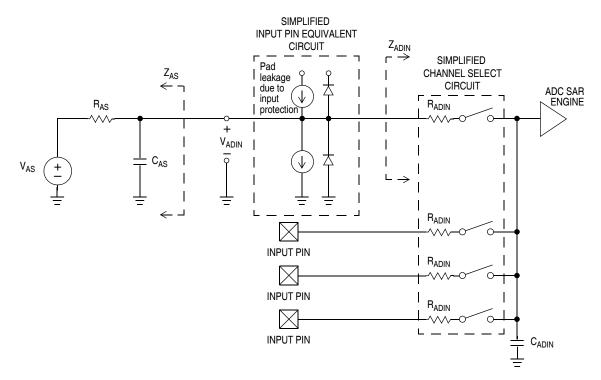


Figure 14. ADC Input Impedance Equivalency Diagram

Table 13. 3 V 10-Bit ADC Characteristics

Characteristic	Conditions	Symbol	Min	Typical ¹	Max	Unit	Comment
Supply current ADLPC = 1 ADLSMP = 1 ADCO = 1		I _{DDAD}	_	120	_	μА	
Supply current ADLPC = 1 ADLSMP = 0 ADCO = 1		I _{DDAD}	_	202	_	μΑ	
Supply current ADLPC = 0 ADLSMP = 1 ADCO = 1		I _{DDAD}	_	288	_	μΑ	
Supply current ADLPC = 0 ADLSMP = 0 ADCO = 1		I _{DDAD}	_	532	646	μА	
ADC asynchronous	High speed (ADLPC=0)		2	3.3	5	MHz	t _{ADACK} =
clock source	Low power (ADLPC=1)	† _{ADACK}	1.25	2	3.3	IVIMZ	1/f _{ADACK}



Table 13. 3 V 10-Bit ADC Characteristics (continued)

Characteristic	Conditions	Symbol	Min	Typical ¹	Max	Unit	Comment
Conversion time (including sample time)	Short sample (ADLSMP=0)		_	20	_	ADCK cycles	See MC9S08QA4 Series Reference Manual for
	Long sample (ADLSMP=1)	t _{ADC}	_	40	_		
Sample time	Short sample (ADLSMP=0)	t _{ADS}	_	3.5	_	ADCK	
	Long sample (ADLSMP=1)		_	23.5	_	cycles	conversion time variances
T-4-1 di4- d	10-bit mode	L	_	±1.5	±3.5	1.002	Includes
Total unadjusted error	8-bit mode	E _{TUE}	_	±0.7	±1.5	LSB ²	quantization
5	10-bit mode			±0.5	±1.0		Monotonicity
Differential non-linearity	8-bit mode	DNL	_	±0.3	±0.5	LSB ²	and no missing codes guaranteed
Integral non-linearity	10-bit mode	INL	_	±0.5	±1.0	- LSB ²	
integral non-linearity	8-bit mode		1	±0.3	±0.5		
Zero-scale error	10-bit mode	- E _{ZS}	1	±1.5	±2.1	- LSB ²	$V_{ADIN} = V_{SS}$
Zero-scale error	8-bit mode		-	±0.5	±0.7		
Full-scale error	10-bit mode	- E _{FS}	0	±1.0	±1.5	LSB ²	$V_{ADIN} = V_{DD}$
Tuli soule error	8-bit mode	-FS	0	±0.5	±0.5	LOD	v _{ADIN} = v _{DD}
Quantization error	10-bit mode	E _Q	1	_	±0.5	- LSB ²	
Quantization enoi	8-bit mode	LQ.	1	_	±0.5		
Input loakage error	10-bit mode	E _{IL}	0	±0.2	±4	LSB ²	Pad leakage ³ *
Input leakage error	8-bit mode	⊢IL	0	±0.1	±1.2	LOD	R _{AS}
Temp sensor slope	–40°C − 25°C		_	1.646	_	mV/°C	
	25°C – 85°C	m		1.769		11117/ 0	
Temp sensor voltage	25°C	V _{TEMP25}	_	701.2	_	mV	

Typical values assume V_{DD} = 3.0 V, Temp = 25°C, f_{ADCK} = 1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

3.11 Flash Specifications

This section provides details about program/erase times and program-erase endurance for the flash memory.

² 1 LSB = $(V_{REFH} - V_{REFL})/2^N$

³ Based on input pad leakage current. Refer to pad electricals.

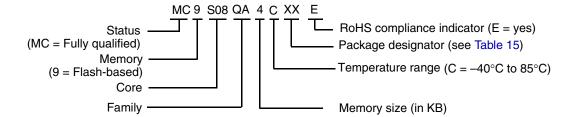


4 Ordering Information

This section contains ordering numbers for MC9S08QA4 series devices. See below for an example of the device numbering system.

Memory **Package Device Number** Flash **RAM Type** Designator **Document No.** 8 DFN FQ 98ARL10557D MC9S08QA4 4 KB 256 bytes 8 PDIP PA 98ASB42420B MC9S08QA2 2 KB 160 bytes 8 NB SOIC DN 98ASB42564B

Table 15. Device Numbering System

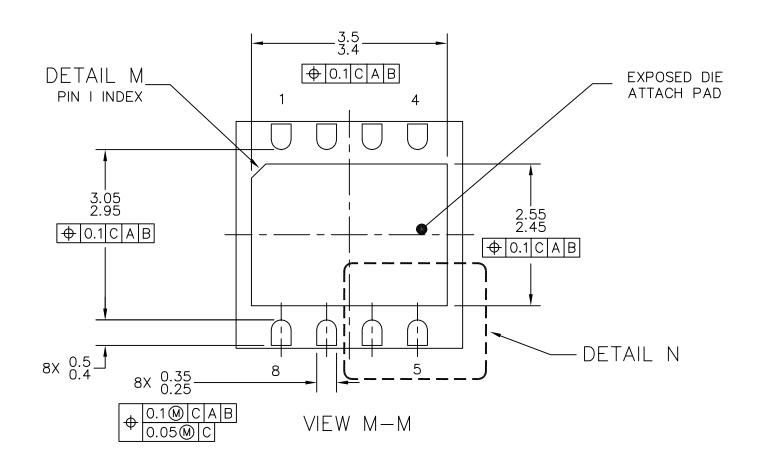


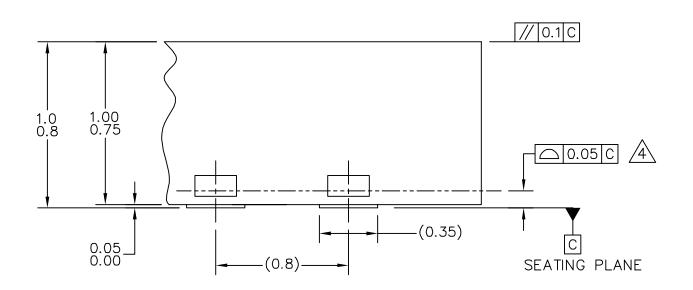
5 Mechanical Drawings

The following pages contain mechanical specifications for MC9S08QA4 series package options.

- 8-pin DFN (plastic dual in-line pin)
- 8-pin NB SOIC (narrow body small outline integrated circuit)
- 8-pin PDIP (plastic dual in-line pin)







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8 TERMINAL 0.8 PITCH $(4 \times 4 \times 1)$		DOCUMENT NO): 98ARL10557D	REV: B
		CASE NUMBER	2: 1452–02	28 DEC 2005
		STANDARD: NO	N-JEDEC	



NOTES:

- 1. ALL DIMENSIONS ARE IN MILLIMETERS.
- 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
- 3. THE COMPLETE JEDEC DESIGNATOR FOR THIS PACKAGE IS: HP-VFDFP-N.

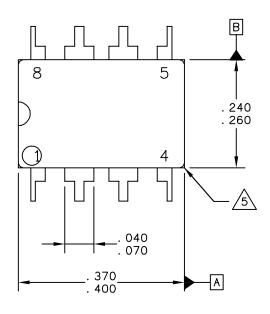
4.

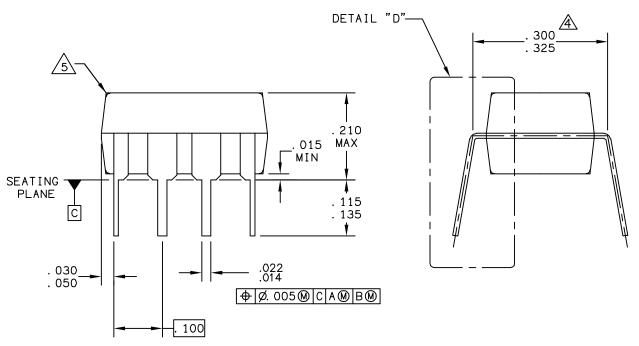
COPLANARITY APPLIES TO LEADS AND DIE ATTACH PAD.

5. MIN. METAL GAP SHOULD BE 0.2MM.

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TITLE:THERMALLY ENHANCED DUAL		DOCUMENT NO: 98ARL10557D		REV: B
		CASE NUMBER	: 1452–02	28 DEC 2005
8 TERMINAL, O. 8 PITCH(4	X 4 X 1)	STANDARD: NO	N-JEDEC	•

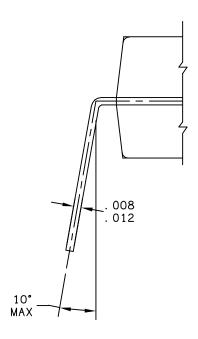






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TITLE:		DOCUMENT NO): 98ASB42420B	REV: N
8 LD PDIP		CASE NUMBER: 626-06 19 MAY		19 MAY 2005
		STANDARD: NO	N-JEDEC	





DETAIL "D"

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TITLE:		DOCUMENT NO): 98ASB42420B	REV: N	
8 LD PDIP		CASE NUMBER: 626-06 19 MAY 200			
		STANDARD: NO	N-JEDEC		



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M - 1994.
- 2. ALL DIMENSIONS ARE IN INCHES.
- 3. 626-03 TO 626-06 OBSOLETE. NEW STANDARD 626-07.
- *A*. DIMENSION TO CENTER OF LEAD WHEN FORMED PARALLEL.
- *f*5. PACKAGE CONTOUR OPTIONAL (ROUND OR SQUARE CONERS).

STYLE 1:

PIN AC IN GROUND 1. 5. OUTPUT 2. DC + IN6. 3.

DC - IN AUXILIARY 7.

AC IN 4. 8. VCC

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TITLE:		DOCUMENT NO): 98ASB42420B	REV: N
8 LD PDIP		CASE NUMBER	R: 626–06	19 MAY 2005
		STANDARD: NO	N-JEDEC	



STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE #1 2. COLLECTOR, #2 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #2 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1
STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE	STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE
STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1	STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON
STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON

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		STANDARD: JEDEC MS-012AA		





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